

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application.

1. – 15. (Cancelled)

16. (New) A method comprising:

applying a photoresist layer to a first substrate to protect an active portion having a first circuit;

etching a portion of the first substrate that is not protected by the photoresist layer;

bonding the first substrate to a second substrate after said etching; and

thinning the first substrate to remove an unsupported bevel portion of the first substrate.

17. (New) The method of claim 16, wherein said etching comprises etching a curved portion that extends beyond a flat portion having the active portion, the curved portion curved so that it would not have been supported by the second substrate when the first and second substrates were bonded.

18. (New) The method of claim 16, wherein said applying comprises applying the photoresist layer to a wafer.

19. (New) The method of claim 16, wherein said bonding comprises bonding the active portion of the first substrate to the second substrate.

20. (New) The method of claim 16, wherein said bonding comprises bonding the first substrate to a second substrate having a second circuit.
21. (New) The method of claim 16, further comprising stripping the photoresist layer after said etching.
22. (New) The method of claim 16, wherein said etching comprises dry etching.
23. (New) The method of claim 16, wherein said etching comprises wet etching.
24. (New) The method of claim 16, wherein said thinning comprises grinding the first substrate.
25. (New) The method of claim 16, wherein said applying comprises applying the photoresist layer to a flat area just before a curved area.
26. (New) A method comprising:

removing a first portion of an unsupported component from a first substrate having an active component;

bonding the active component of the first substrate to a second substrate; and

thinning the first substrate to remove a second portion of the unsupported component of the first substrate.
27. (New) The method of claim 26, wherein said removing the first portion of the unsupported component comprises:

applying a photoresist layer to cover the active component of the first substrate;
and

etching the first portion of the unsupported component of the first substrate.

28. (New) The method of claim 26, wherein said removing the first portion of the unsupported component comprises etching a curved portion that extends beyond a flat portion having the active portion, the curved portion curved so that it would not have been supported by the second substrate when the first and second substrates were bonded.
29. (New) The method of claim 26, wherein said bonding comprises bonding wafers.
30. (New) The method of claim 26, wherein said bonding comprises bonding the active component of the first substrate to a second substrate having a circuit.
31. (New) The method of claim 26, wherein said thinning the first substrate comprises grinding the first substrate.
32. (New) A method comprising:

forming a layer over a first circuit in an active portion of a first substrate;

removing a portion of the first substrate that is not under the layer;

removing the layer;

bonding the active portion of the first substrate to a second substrate having a second circuit after said removing the layer; and

thinning the first substrate to remove a portion that is not supported by the second substrate.

33. (New) The method of claim 32, wherein said removing the portion of the first substrate comprises removing a curved portion that extends beyond a flat portion having the active portion, the curved portion curved so that it would not have been supported by the second substrate when the first and second substrates are bonded.
34. (New) The method of claim 32, wherein said forming comprises applying a photoresist layer to a wafer.
35. (New) The method of claim 32, wherein said removing the portion of the first substrate comprises etching the first substrate, wherein said removing the layer comprises stripping the layer, and wherein said thinning the first substrate comprises grinding the first substrate.